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## Plasma enhanced atomic layer deposition of Fe<sub>2</sub>O<sub>3</sub> thin films

Ranjith K. Ramachandran, Jolien Dendooven, and Christophe Detavernier\*

Department of Solid State Sciences, COCOON, Ghent University, Krijgslaan 281/S1, 9000 Ghent, Belgium,

A series of depositions were carried out at 200 °C with different number of ALD cyles. The thickness of the films was measured with X-ray reflectivity (XRR). Excellent fits for the XRR spectra were obtained by assuming the film density equal to the one of bulk  $\alpha - \text{Fe}_2\text{O}_3$  (5.27g/cm<sup>3</sup>)<sup>1</sup>. X-ray fluorescence measurements were done on each sample and a linear relationship was obtained by plotting the integrated area under the Fe K $\alpha$  peak against the thickness (Figure S1). This linear relationship was used for extracting the thickness of the films deposited at and above 350 °C and the thicker films deposited at 300 °C.



**Figure S1.** XRR (top) and XRF (bottom left) signals of  $Fe_2O_3$  thin films with different thicknesses deposited on SiO<sub>2</sub> substrates at 200 °C. The thickness against the integrated XRF intensity over Fe K $\alpha$  signal is plotted in the bottom right figure.

## References

1 M. Lie, H. Fjellvåg, and a. Kjekshus, *Thin Solid Films*, 2005, **488**, 74–81